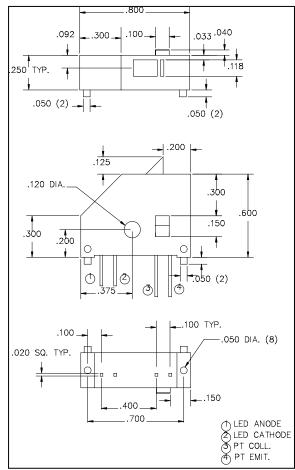


FEATURES:

- Single Emitter Bar Code / Fine Line Sensor
- Better than 0.010" Resolution
- Compact Size
- Easily Ganged for Multiple Channels

PRODUCT DESCRIPTION

The OTBC-04XX series combine a single emitter with a phototransistor in a compact low cost package containing a lens and aperture. The OTBC-0480 has a 940 nm infrared emitter and a phototransistor. The OTBC-0490 has a 660 nm visible red emitter and a phototransistor. The OTBC-0482 has a 940 nm infrared emitter and a phototransistor with an ambient



light filter, for use in high ambient light conditions. These devices are easily ganged for multi-channel applications. Consult factory for custom apertures, emitters, or sensors.

Absolute Maximum Ratings

General	
Storage Temperature Range	55°C to +100°C
Operating Temperature Range	40°C to +85°C
Lead Soldering Temperature (1/16" from case	
for 5 seconds soldering iron, 10 seconds flow soldering)	260°C
Infrared Emitter (940 nm)	
Reverse Voltage	5 V
Continuous Forward Current	120 mA
Peak Forward Current	1.5 A
Power Dissipation	100 mW
Visible Emitter (660 nm)	
Reverse Voltage	4 V
Continuous Forward Current	40 mA
Peak Forward Current	300 mA
Power Dissipation	100 mW
Phototransistor	
Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Power Dissipation (Derate 2.4 mW/°C above 25°C)	100 mW

RHOPOINT COMPONENTS LTD

Holland Road, Hurst Green, Oxted, Surrey, RH8 9AX Tel: +44 (0)1883 717988 Fax: +44 (0)1883 712938

Product Specifications (T_A = 25°C unless noted)

Infrared Emitter (OTBC-048X)

Parameter	Symbol	Min	Тур	Max	Units
Forward Voltage (I _F = 50 mA)	V_{F}		1.3	1.45	V
Reverse Current (V _R = 5 V)	I _R			100	μΑ
Peak Wavelength (I _F = 20 mA)	λ_{P}		940		nm
Radiant Intensity (I _F = 20 mA)		1.3	2.5		mW/sr
Spectral Bandwidth at 50% (I _F = 20 mA)	Δλ		50		nm
Half Intensity Beam Angle	θ		10		Degrees

Visible Emitter (OTBC-049X)

Parameter	Symbol	Min	Тур	Max	Units
Forward Voltage (I _F = 20 mA)	V_{F}		1.8	2.4	V
Reverse Current (V _R = 4 V)	I _R			100	μΑ
Peak Wavelength (I _F = 20 mA)	λ _P		660		nm
Luminous Intensity (I _F = 20 mA)	I _V	250	500		mcd
Spectral Bandwidth at 50% (I _F = 20 mA)	Δλ		20		nm
Half Intensity Beam Angle	θ		10		Degrees

Phototransistor (OTBC-04X0)

Parameter	Symbol	Min	Тур	Max	Units
Light Current (Ee=0.1mW/cm ² , V _{CE} =5V)	I _{CE(ON)}	1	2.8		mA
Dark Current (Ee=0, V _{CE} =10V)	I _{CE0}			100	nA
Saturation Voltage (I _C =0.5mA, Ee=0.1mW/cm ²)	V _{CE(SAT)}			0.4	V
Rise Time (V_{CC} =5 V , R_L =1 $k\Omega$, I_C =1 mA)	T _r		15		μS
Fall Time (V_{CC} =5 V , R_L =1 $k\Omega$, I_C =1 mA)	T _f		15		μS

Coupled Characteristics

Parameter	Symbol	Min	Тур	Max	Units
Light Current ($I_F = 20 \text{ mA}, V_{CE} = 5V, d = 0.125 \text{ in}$) ¹	I _{CE(ON)}	5	10		μА
Dark Current ($I_F = 0 \text{ mA}, V_{CE} = 5V$)	I _{CE0}			200	nA
6 dB Bandwidth		3			kHz

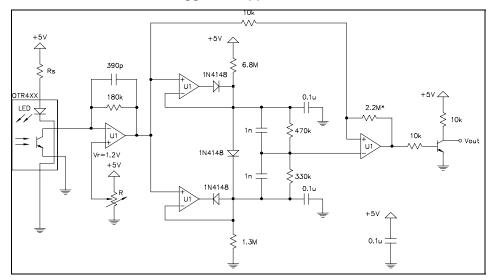
¹Reflecting surface is Eastman Kodak neutral white test card having a 90% diffused reflectance.

Reflective Surface

Parameter	Symbol	Min	Тур	Max	Units
Element Contrast		(80%)			%
Diffused Reflectance		(90%)			%
Element Width	W_N	0.010			in
Narrow Element to Narrow Space Ratio			0.95		
Depth of Field	d	0.090	0.125	0.160	in

Email: sales@rhopointcomponents.com Web: www.rhopointcomponents.com

Suggested Application Circuit



The above circuit represents an adaptive dual peak detector with a first stage transimpedance amplifier. This circuit is recommended for typical bar code or fine element sensing applications using the OTBC-04XX series optic heads. The first amplifier servers as a current-to-voltage amplifier (transimpedance). The second part of the circuit provides positive and negative peak detection. The peak voltages are temporarily stored in the 0.1 μ F capacitors. The comparator reference is approximately 45% of the peak-to-peak amplitude. This, in effect, provides an adaptive threshold to the comparator based on the voltage peaks of the incoming signal. The 2.2 M Ω resistor on the last stage (indicated with an *) sets the positive feedback, and combined with the 10 k Ω input resistor the hysterisis is set to approximately 25 mV. Setting the 2.2 M Ω resistor to 100 k Ω will increase the hysterisis to 500 mV, but response will be sacrificed. V_{out} is low for reflectance and high (+5V) for no reflectance (i.e., sensing a dark mark).

Ordering Information

